

KEC

SEMICONDUCTOR
TECHNICAL DATA

KDV273UL

VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

VCO FOR UHF/VHF BAND.

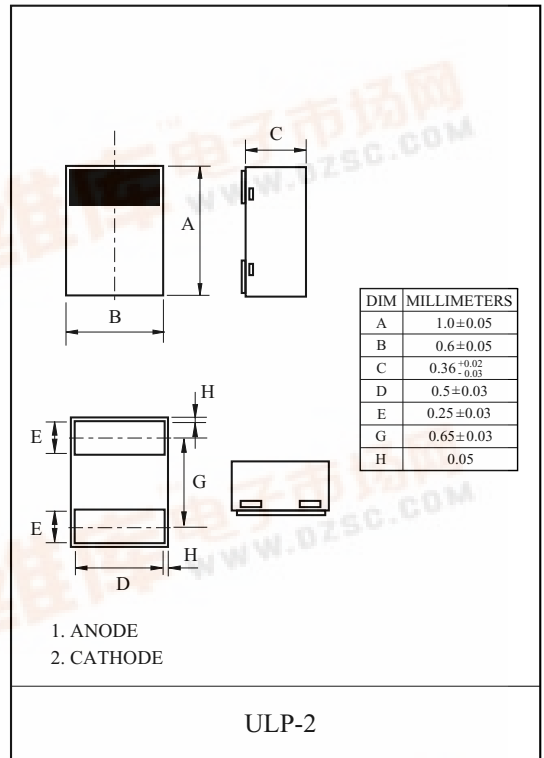
FEATURES

- High Capacitance Ratio : $C_{1V}/C_{4V}=2.0$ (Typ.)
- Low Series Resistance : $r_s=0.39\ \Omega$ (Typ.)

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

TENTATIVE



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R=1\ \mu A$	10	-	-	V
Reverse Current	I_R	$V_R=10V$	-	-	10	nA
Capacitance	C_{1V}	$V_R=1V, f=1MHz$	15	16	17	pF
	C_{4V}	$V_R=4V, f=1MHz$	7.3	8.0	8.7	
Capacitance Ratio	K	-	1.8	2.0	-	
Series Resistance	r_s	$V_R=1V, f=470MHz$	-	0.39	0.5	Ω

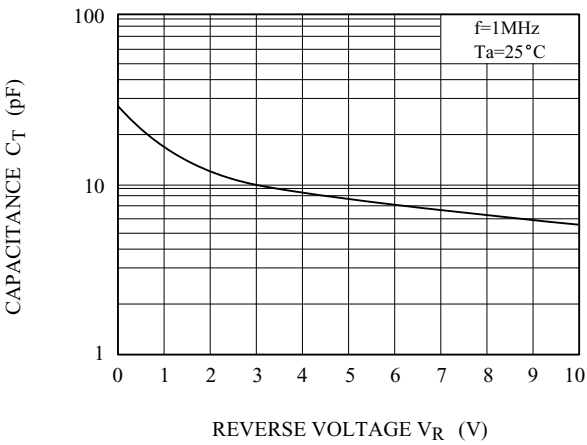
Marking

Type Name



KDV273UL

$C_T - V_R$



$I_R - V_R$

